RoHS Compliant

Magnachip

MDIS1903

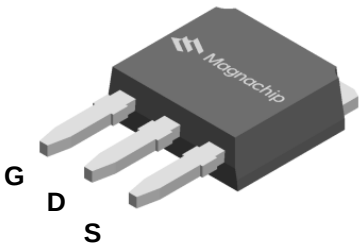
Single N-channel Trench MOSFET 100V, 12.8A, 105mΩ

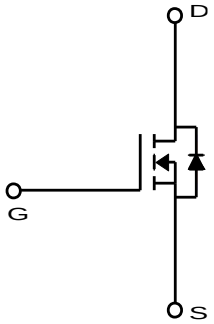
General Description

The MDIS1903 uses advanced Magnachip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDIS1903 is suitable device for DC to DC converter and general purpose applications.

Features

- V_{DS} = 100V
- I_D = 12.8A @V_{GS} = 10V
- $R_{DS(ON)\ (MAX)}$
  < 105mΩ @V_{GS} = 10V
  < 110mΩ @V_{GS} = 6.0V





Absolute Maximum Ratings (Tc = 25ºC)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (1)	T_C=25ºC	I_D	12.8	A
	T_C=70ºC		10.3	
Pulsed Drain Current		I_{DM}	40	A
Power Dissipation	T_C=25ºC	P_D	36.8	W
	T_C=70ºC		23.6	
Single Pulse Avalanche Energy (2)		E_{AS}	21	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	ºC

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient (1)	$R_{\theta JA}$	52	ºC/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.4	

Ordering Information

Part Number	Temp. Range	Package	Packing	Rohs Status
MDIS1903TH	-55~150°C	TO-251-VS(IPAK)	Tube	Halogen Free

Electrical Characteristics (T_J =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D = 250μA, V_{GS} = 0V	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	2.0	3.0	
Drain Cut-Off Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V	-	-	1	μA
Gate Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±0.1	
Drain-Source ON Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 10A	-	85	105	mΩ
		V_{GS} = 6.0V, I_D = 10A	-	90	110	
Forward Transconductance	g_{fs}	V_{DS} = 10V, I_D = 10A	-	17	-	S
Dynamic Characteristics						
Total Gate Charge	$Q_{g(10V)}$	V_{DS} = 50.0V, I_D = 10A, V_{GS} = 10V	-	8.8		nC
Gate-Source Charge	Q_{gs}		-	1.7		
Gate-Drain Charge	Q_{gd}		-	2.3		
Input Capacitance	C_{iss}	V_{DS} = 25.0V, V_{GS} = 0V, f = 1.0MHz	-	475	800	pF
Reverse Transfer Capacitance	C_{rss}		-	20	-	
Output Capacitance	C_{oss}		-	60	-	
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = 10V, V_{DS} = 50V, I_D = 10A , R_G = 3.0Ω	-	6.8	-	ns
Rise Time	t_r		-	10.6	-	
Turn-Off Delay Time	$t_{d(off)}$		-	16.2	-	
Fall Time	t_f		-	5.5	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V_{SD}	I_S = 10A, V_{GS} = 0V	-	0.75	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 10A, dI/dt = 100A/μs	-	42.0	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	69.0	-	nC

Note :

1. Surface mounted FR-4 board by JEDEC (jesd51-7)
2. E_{AS} is tested at starting Tj = 25℃, L = 1.0mH, I_{AS} = 6.5A, V_{DD} = 50V, V_{GS} = 10V

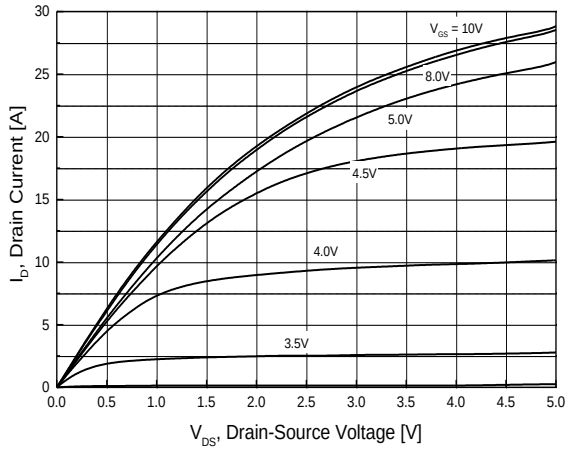


Fig.1 On-Region Characteristics

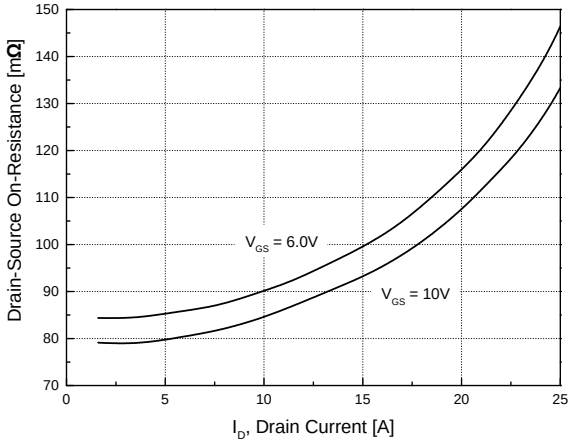


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

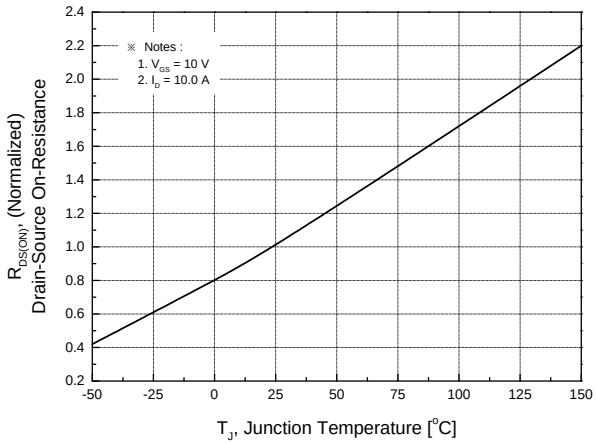


Fig.3 On-Resistance Variation with Temperature

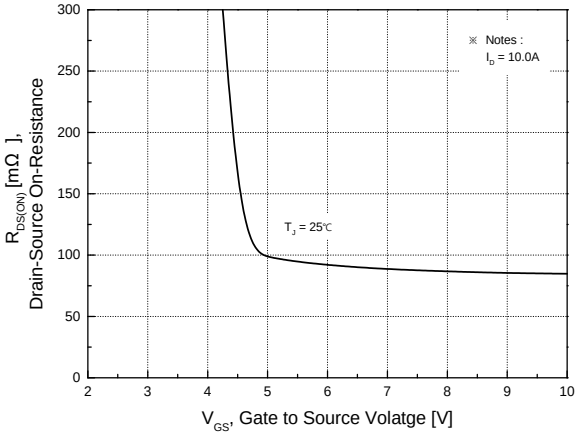


Fig.4 On-Resistance Variation with Gate to Source Voltage

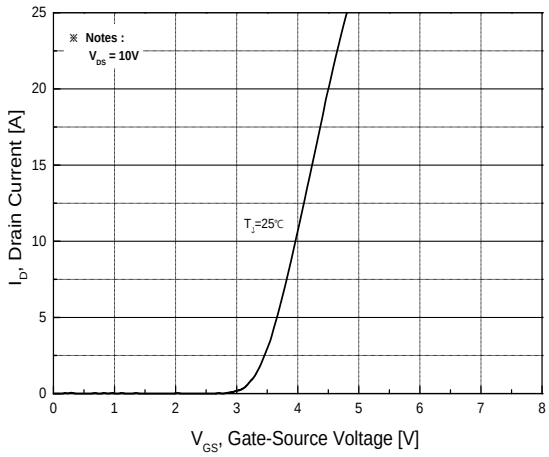


Fig.5 Transfer Characteristics

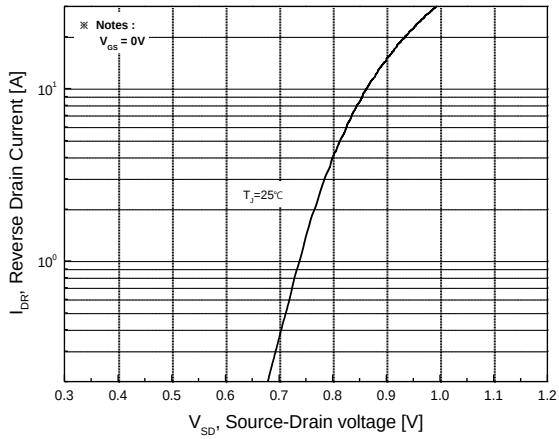


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

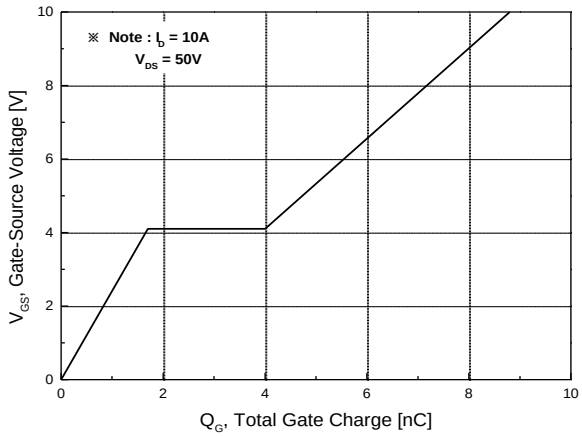


Fig.7 Gate Charge Characteristics

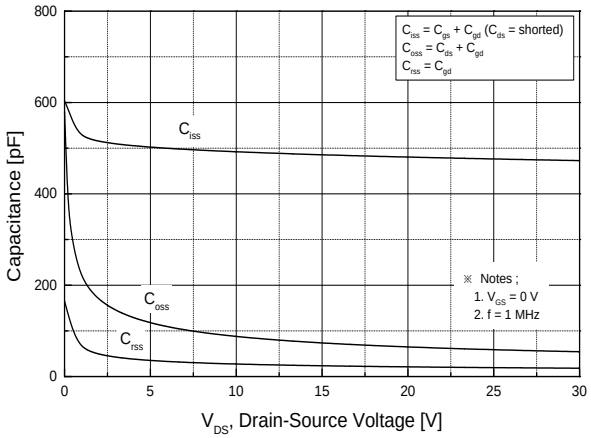


Fig.8 Capacitance Characteristics

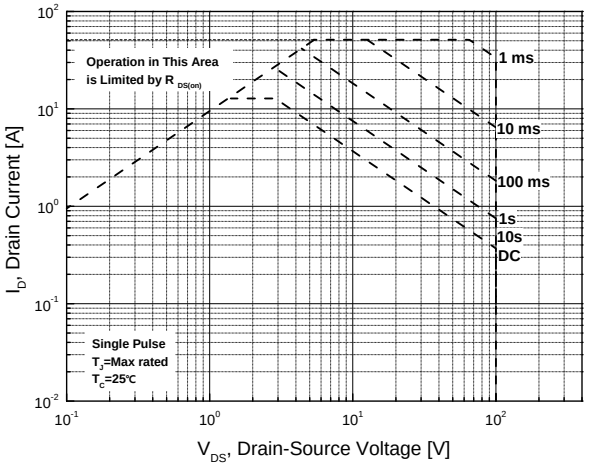


Fig.9 Maximum Safe Operating Area

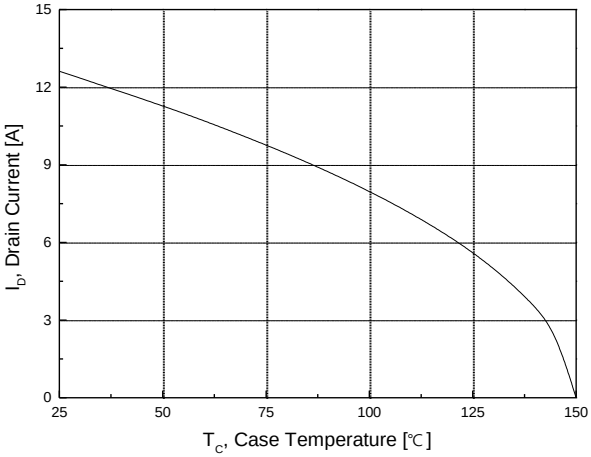


Fig.10 Maximum Drain Current vs. Case Temperature

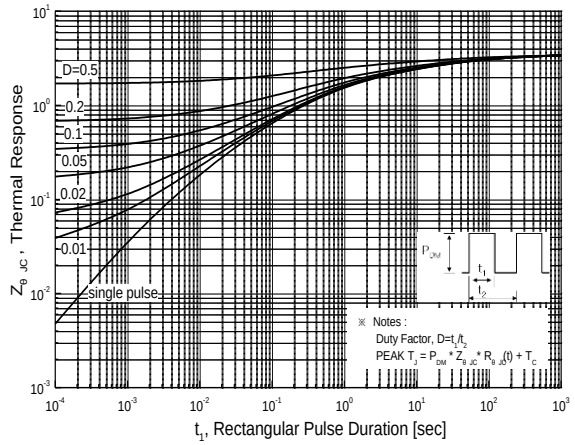
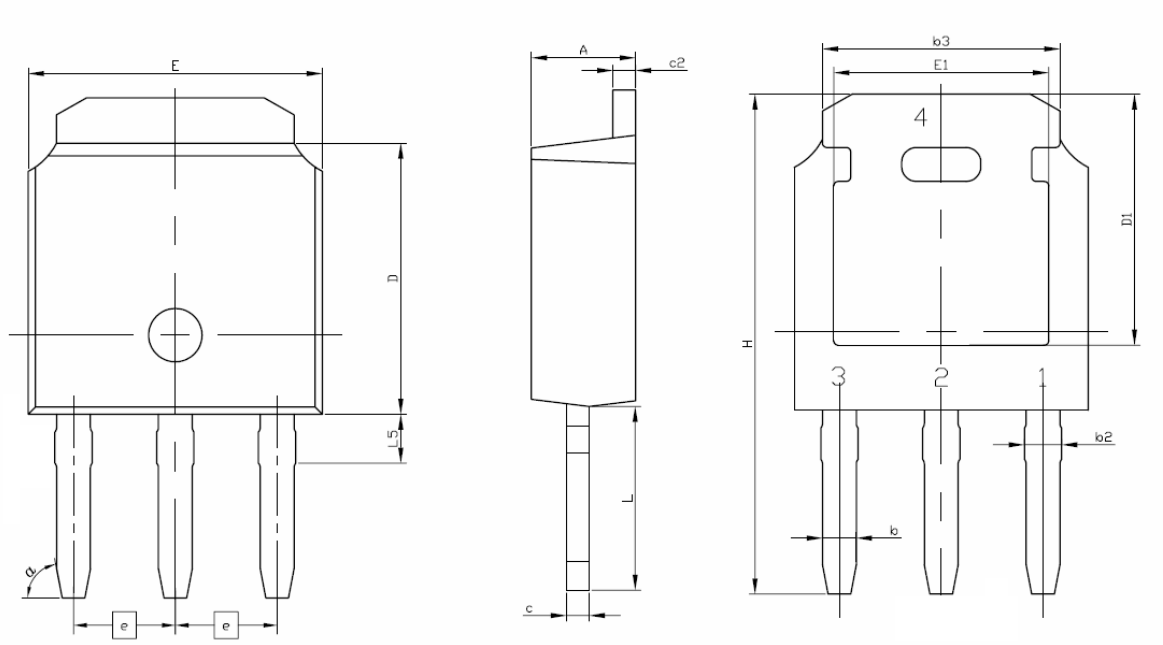


Fig.11 Transient Thermal Response Curve

Package Dimension

TO-251-VS (IPAK)

Dimensions are in millimeters, unless otherwise specified



Symbol	MILLIMETERS	
	Minimum	Maximum
A	2.18	2.39
b	0.64	0.89
b2	0.76	1.14
b3	4.95	5.46
c	0.40	0.61
c2	0.40	0.61
D	5.97	6.223
D1	5.10	-
e	2.286 BSC	
E	6.35	6.73
E1	4.32	-
H	10.26	11.45
L	3.98	4.28
L5	-	1.23

Note : Package body size, length and width do not include mold flash, protrusions and gate burrs.

DISCLAIMER:

The Products are not designed for use in hostile environments, including, without limitation, aircraft, nuclear power generation, medical appliances, and devices or systems in which malfunction of any Product can reasonably be expected to result in a personal injury. Seller's customers using or selling Seller's products for use in such applications do so at their own risk and agree to fully defend and indemnify Seller.